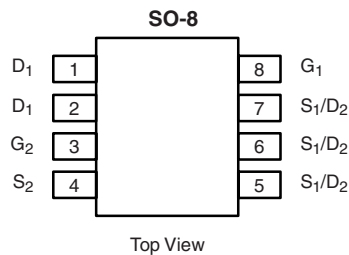


## Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ)
Channel-1	30	0.018 at V <sub>GS</sub> = 10 V	10	6.6
		0.023 at V <sub>GS</sub> = 4.5 V	8.5	
Channel-2		0.018 at V <sub>GS</sub> = 10 V	10.5	8.9
		0.022 at V <sub>GS</sub> = 4.5 V	9.3	

SCHOTTKY PRODUCT SUMMARY		
V <sub>DS</sub> (V)	V <sub>SD</sub> (V) Diode Forward Voltage	I <sub>F</sub> (A)
30	0.50 V at 1.0 A	2.0



Ordering Information: Si4916DY-T1-E3 (Lead (Pb)-free)

### FEATURES

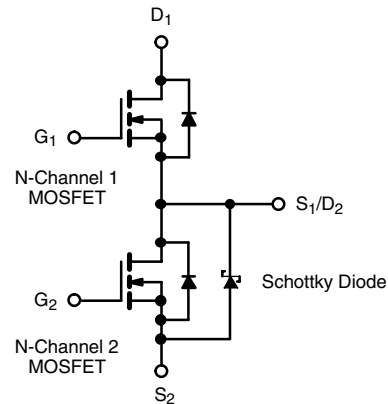
- LITTLE FOOT<sup>®</sup> Plus Integrated Schottky
- 100 % R<sub>g</sub> Tested

### APPLICATIONS

- DC/DC Converters
- Notebook



RoHS  
COMPLIANT



ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	Channel-1	Channel-2	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30		V	
Gate-Source Voltage	V <sub>GS</sub>	20			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a,b</sup>	I <sub>D</sub>	T <sub>C</sub> = 25 °C	10	10.5	A
		T <sub>C</sub> = 70 °C	8	8.3	
		T <sub>A</sub> = 25 °C	7.5 <sup>a, b, c</sup>	7.8 <sup>a, b, c</sup>	
		T <sub>A</sub> = 70 °C	6 <sup>a, b, c</sup>	6.3 <sup>a, b, c</sup>	
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	40	40	A	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	3		3.2
		T <sub>A</sub> = 25 °C	1.7 <sup>a, b, c</sup>		1.8 <sup>a, b, c</sup>
PulseD Source-Drain Current	I <sub>SM</sub>	40	40		mJ
Single-Pulse Avalanche Current	I <sub>AS</sub>	15			
Single-Pulse Avalanche Energy	E <sub>AS</sub>	11.2			
Maximum Power Dissipation <sup>a, b</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	3.3	3.5	W
		T <sub>C</sub> = 70 °C	2.1	2.2	
		T <sub>A</sub> = 25 °C	1.9 <sup>a, b, c</sup>	2.0 <sup>a, b, c</sup>	
		T <sub>A</sub> = 70 °C	1.2 <sup>a, b, c</sup>	1.3 <sup>a, b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

Notes:

- a. Based on T<sub>C</sub> = 25 °C.
- b. Surface Mounted on 1" x 1" FR4 Board.
- c. t = 10 sec.

**THERMAL RESISTANCE RATINGS**

Parameter		Symbol	Channel-1		Channel-2		Unit
			Typ	Max	Typ	Max	
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{thJA}$	54	65	47	60	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	32	38	30	35	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

b. Maximum under Steady State conditions is 112 °C/W for Channel 1 and 107 °C/W for Channel 2.

**MOSFET SPECIFICATIONS**  $T_J = 25$  °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit	
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0$ V, $I_D = 250$ $\mu$ A	Ch-1	30		V	
			Ch-2	30			
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ $\mu$ A	Ch-1		24	mV/°C	
			Ch-2		25		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$V_{DS} = V_{GS}$ , $I_D = 250$ $\mu$ A	Ch-1		- 6	V	
			Ch-2		- 6		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250$ $\mu$ A	Ch-1	1.5	3.0	V	
			Ch-2	1.5	2.7		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0$ V, $V_{GS} = 20$ V	Ch-1		100	nA	
			Ch-2		100		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30$ V, $V_{GS} = 0$ V	Ch-1		1	$\mu$ A	
			Ch-2		100		
		$V_{DS} = 30$ V, $V_{GS} = 0$ V, $T_J = 85$ °C	Ch-1		15		
			Ch-2		2000		
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5$ V, $V_{GS} = 10$ V	Ch-1	20		A	
			Ch-2	20			
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 10$ A	Ch-1		0.0145	0.018	$\Omega$
		$V_{GS} = 10$ V, $I_D = 10.5$ A	Ch-2		0.015	0.018	
		$V_{GS} = 4.5$ V, $I_D = 8.5$ A	Ch-1		0.019	0.023	
		$V_{GS} = 4.5$ V, $I_D = 9.3$ A	Ch-2		0.018	0.022	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15$ V, $I_D = 10$ A	Ch-1		30	S	
		$V_{DS} = 15$ V, $I_D = 10.5$ A	Ch-2		35		
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_S = 1.7$ A, $V_{GS} = 0$ V	Ch-1		0.75	1.1	V
		$I_S = 1$ A, $V_{GS} = 0$ V	Ch-2		0.47	0.5	
<b>Dynamic<sup>a</sup></b>							
Total Gate Charge	$Q_g$	Channel-1 $V_{DS} = 15$ V, $V_{GS} = 4.5$ V, $I_D = 10$ A	Ch-1		6.6	10	nC
			Ch-2		8.9	14	
Gate-Source Charge	$Q_{gs}$	Channel-2 $V_{DS} = 15$ V, $V_{GS} = 4.5$ V, $I_D = - 10.5$ A	Ch-1		2.9		
			Ch-2		3.4		
Gate-Drain Charge	$Q_{gd}$		Ch-1		2.3		
			Ch-2		2.4		
Gate Resistance	$R_g$		Ch-1	0.5	1.9	2.9	$\Omega$
			Ch-2	0.5	2.3	3.5	



<b>MOSFET SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit
<b>Dynamic<sup>a</sup></b>						
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}$ , $R_L = 15\ \Omega$ $I_D \cong 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 6\ \Omega$	Ch-1	8	15	ns
			Ch-2	9	15	
Rise Time	$t_r$		Ch-1	11	18	
			Ch-2	13	20	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 $V_{DD} = 15\text{ V}$ , $R_L = 15\ \Omega$ $I_D \cong 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 6\ \Omega$	Ch-1	21	32	
			Ch-2	27	40	
Fall Time	$t_f$		Ch-1	6	10	
			Ch-2	9	15	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 1.3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	Ch-1	28	40	
		$I_F = 2.2\text{ A}$ , $di/dt = 100\ \mu\text{A}/\mu\text{s}$	Ch-2	24	35	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 1.3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	Ch-1	17		nC
		$I_F = 2.2\text{ A}$ , $di/dt = 100\ \mu\text{A}/\mu\text{s}$	Ch-2	12		
Reverse Recovery Fall Time	$t_a$	$I_F = 1.3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	Ch-1	12		ns
		$I_F = 2.2\text{ A}$ , $di/dt = 100\ \mu\text{A}/\mu\text{s}$	Ch-2	11		
Reverse Recovery Rise Time	$t_b$	$I_F = 1.3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	Ch-1	16		ns
		$I_F = 2.2\text{ A}$ , $di/dt = 100\ \mu\text{A}/\mu\text{s}$	Ch-2	13		

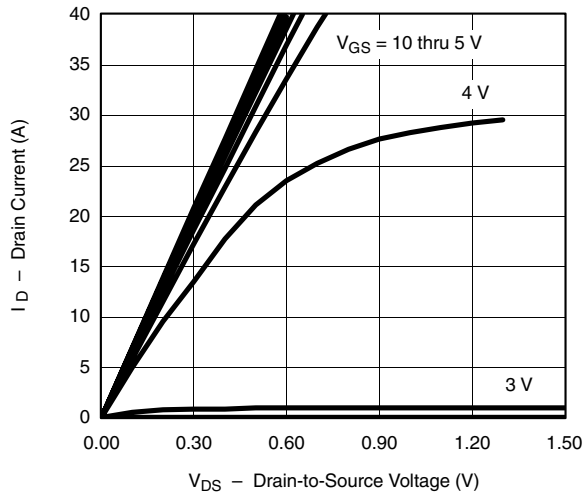
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

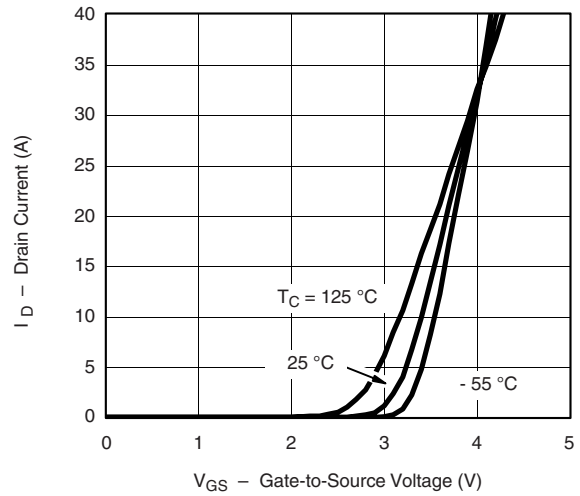
<b>SCHOTTKY SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage Drop	$V_F$	$I_F = 1.0\text{ A}$		0.47	0.50	V
		$I_F = 1.0\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$		0.36	0.42	
Maximum Reverse Leakage Current	$I_{rm}$	$V_r = 30\text{ V}$		0.004	0.100	mA
		$V_r = 30\text{ V}$ , $T_J = 100\text{ }^\circ\text{C}$		0.7	10	
		$V_r = -30\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$		3.0	20	
Junction Capacitance	$C_T$	$V_r = 10\text{ V}$		50		pF

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

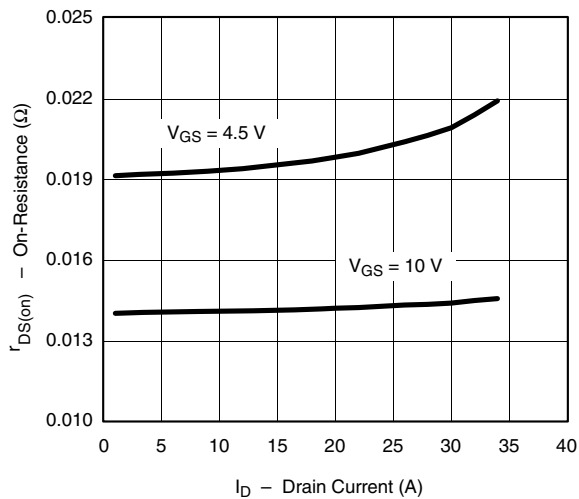
## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



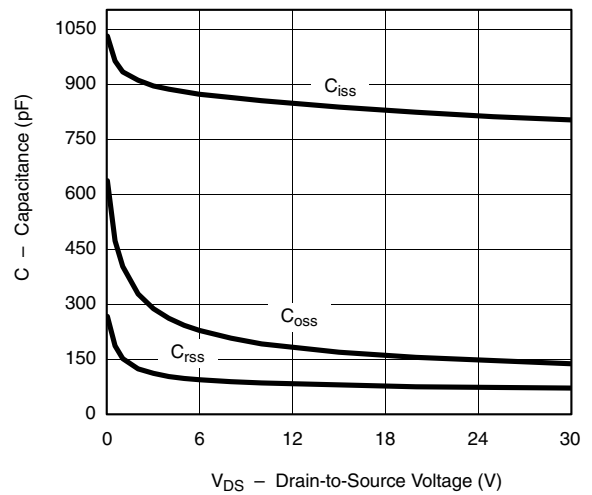
**Output Characteristics**



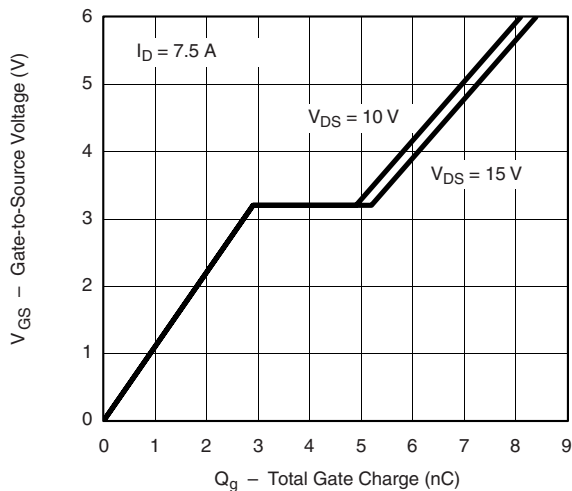
**Transfer Characteristics**



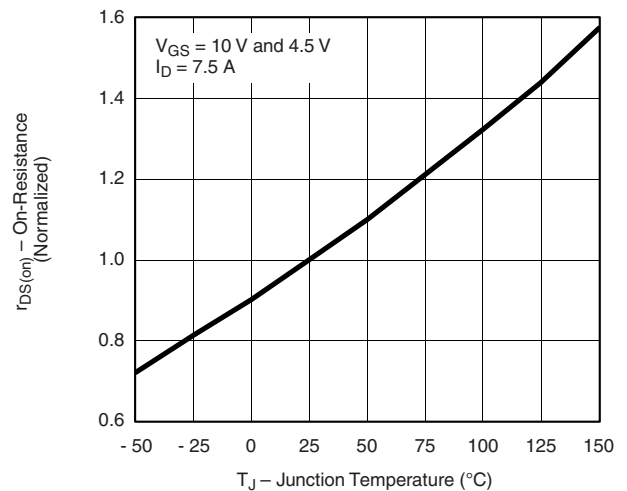
**On-Resistance vs. Drain Current**



**Capacitance**

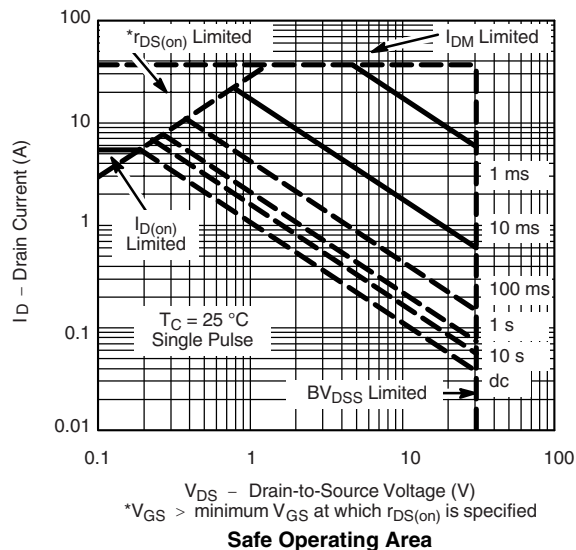
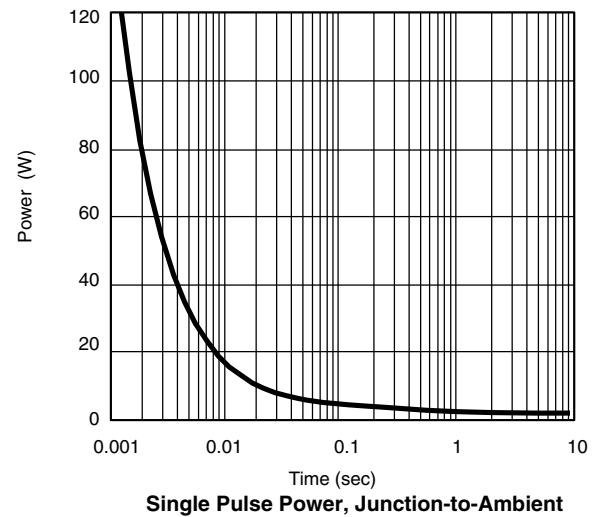
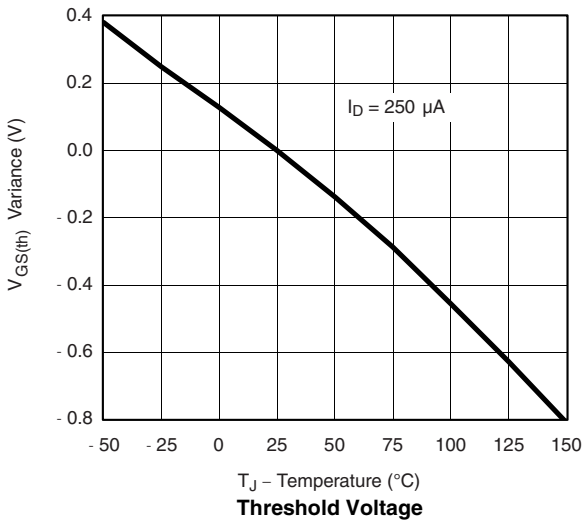
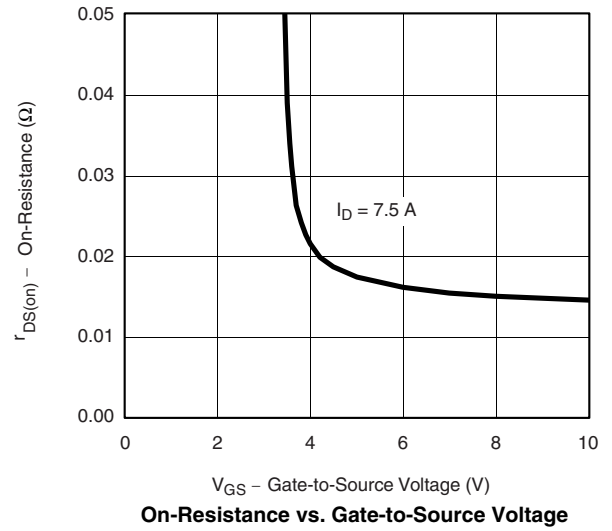
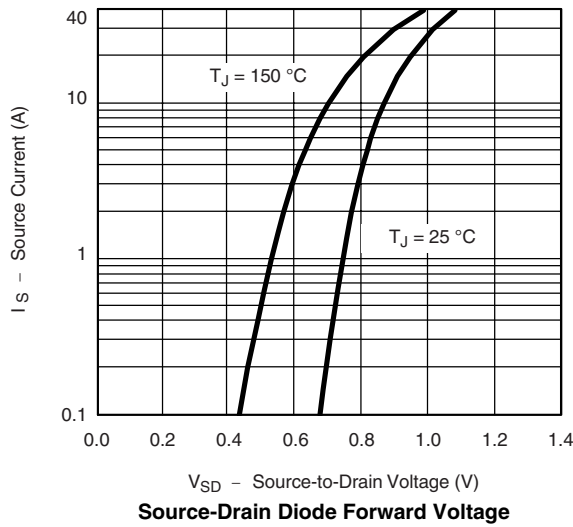


**Gate Charge**

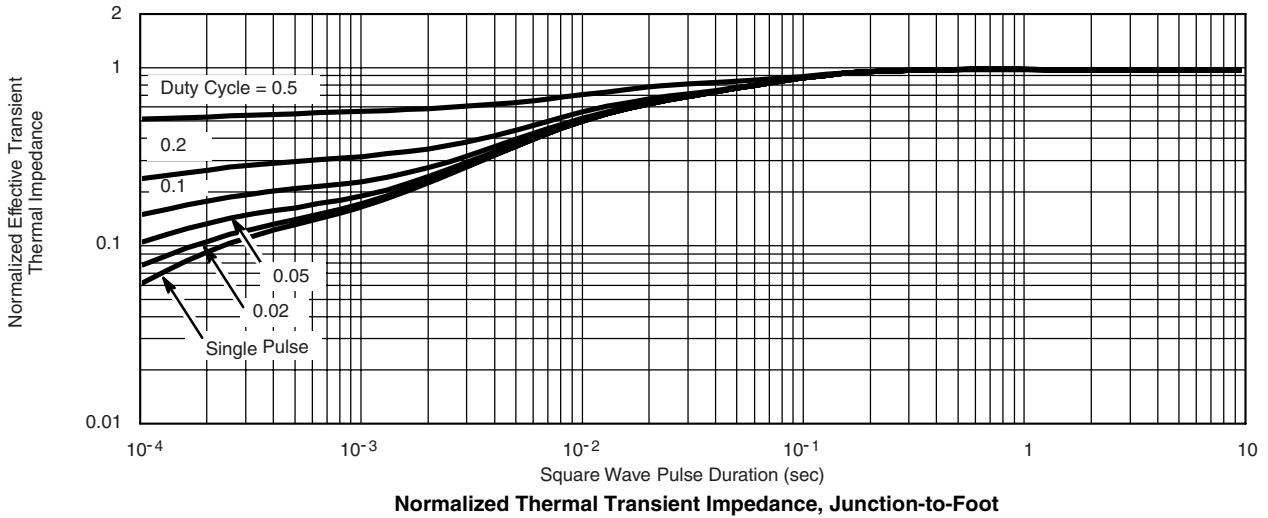
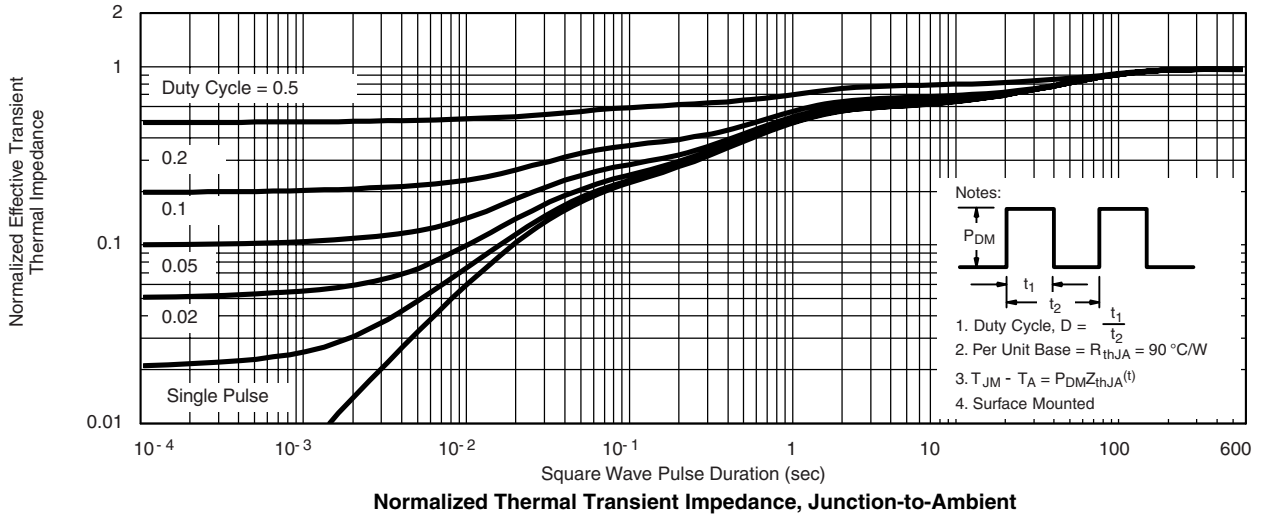


**On-Resistance vs. Junction Temperature**

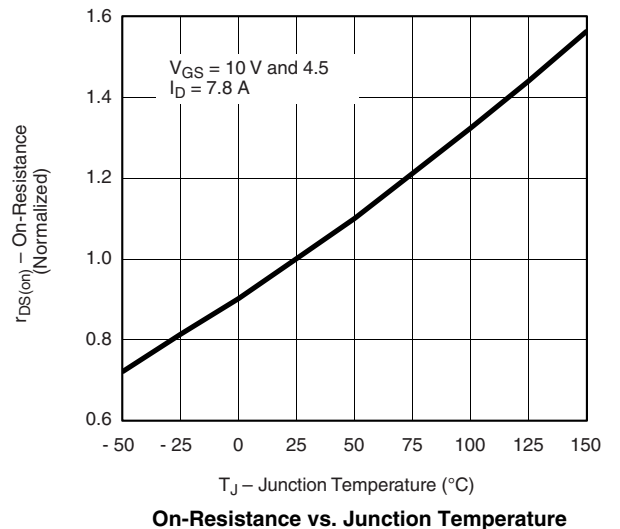
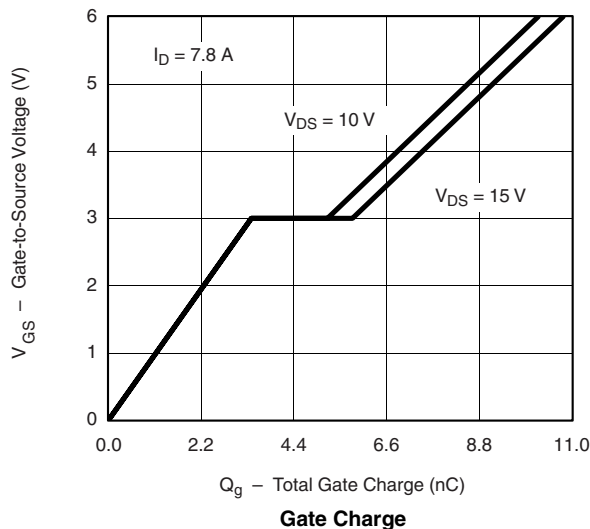
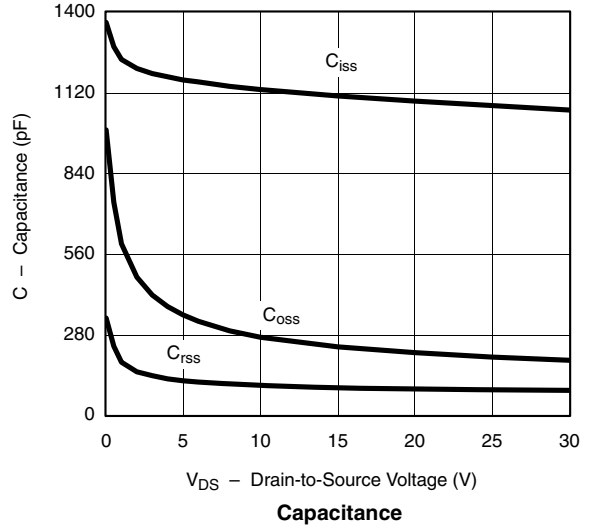
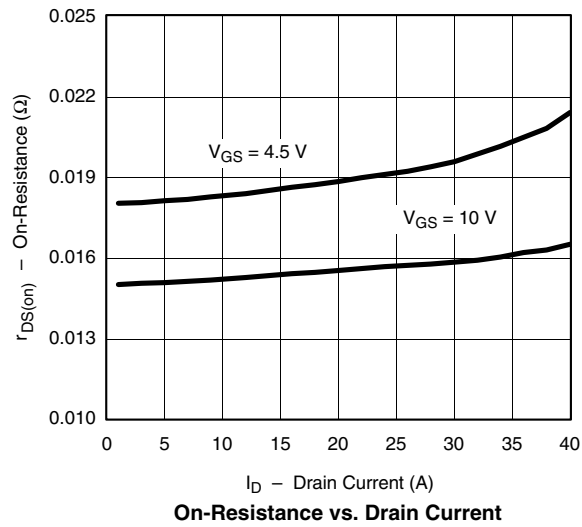
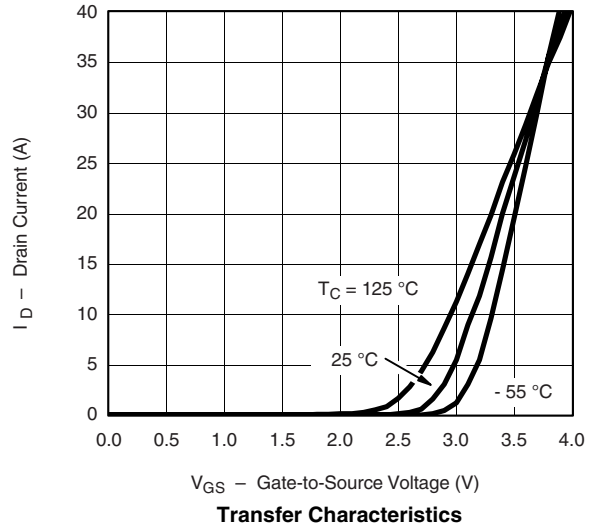
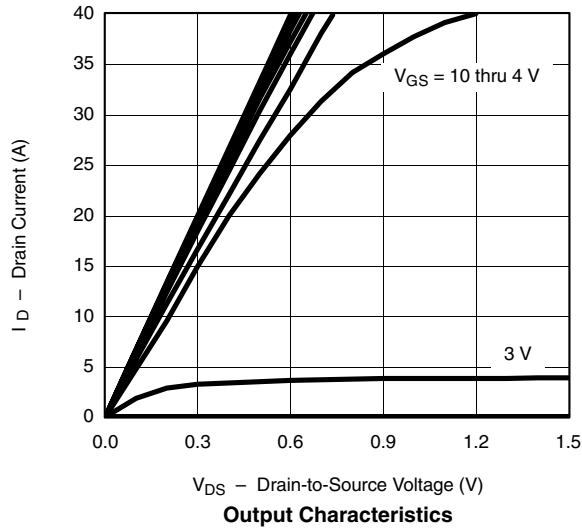
**CHANNEL-1 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



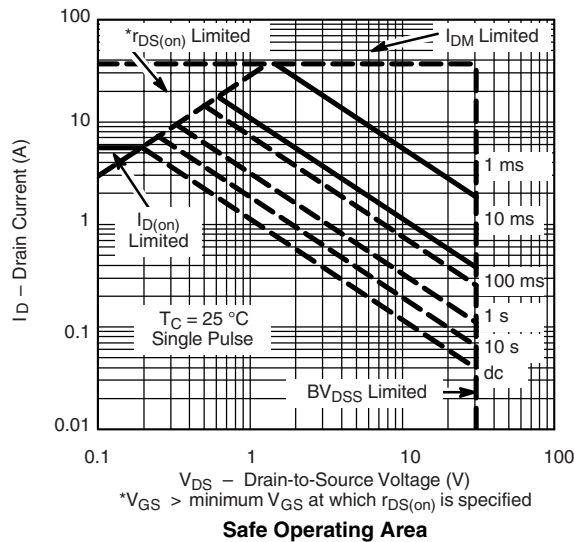
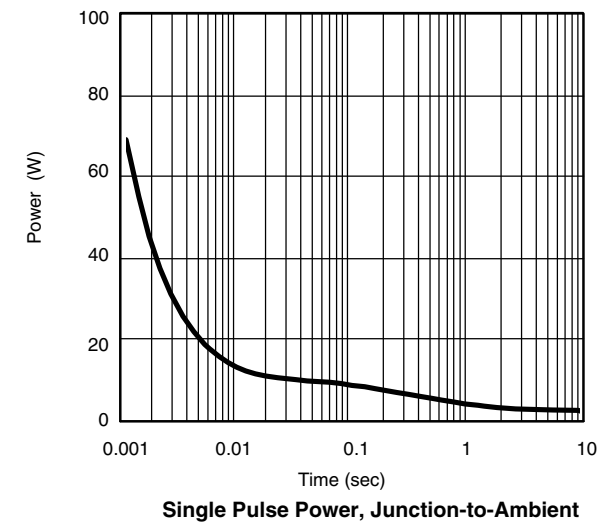
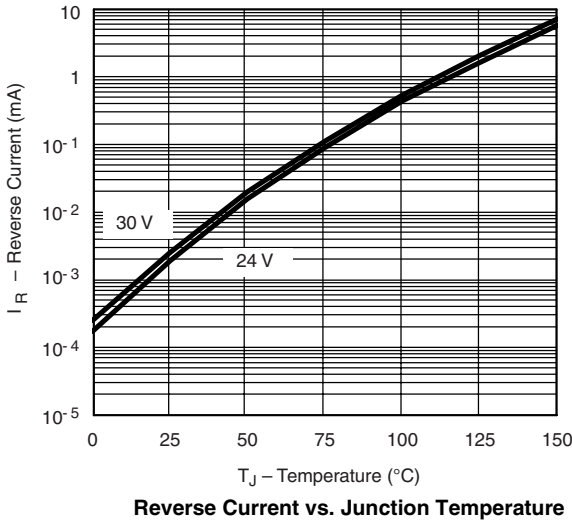
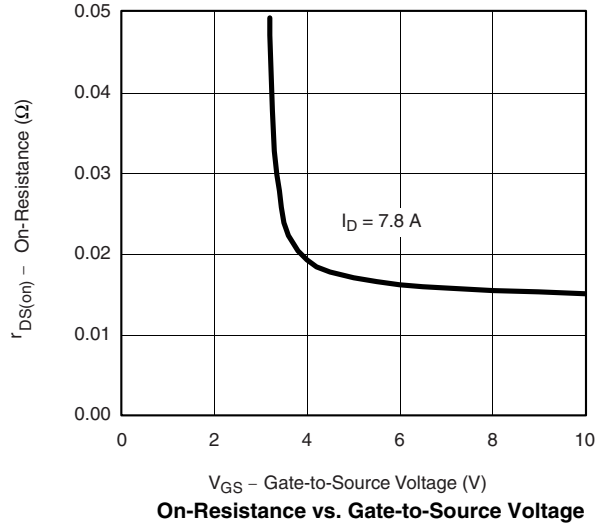
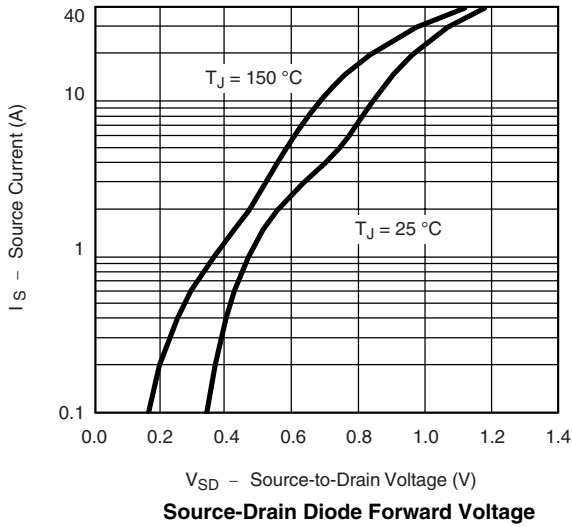
**CHANNEL-1 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

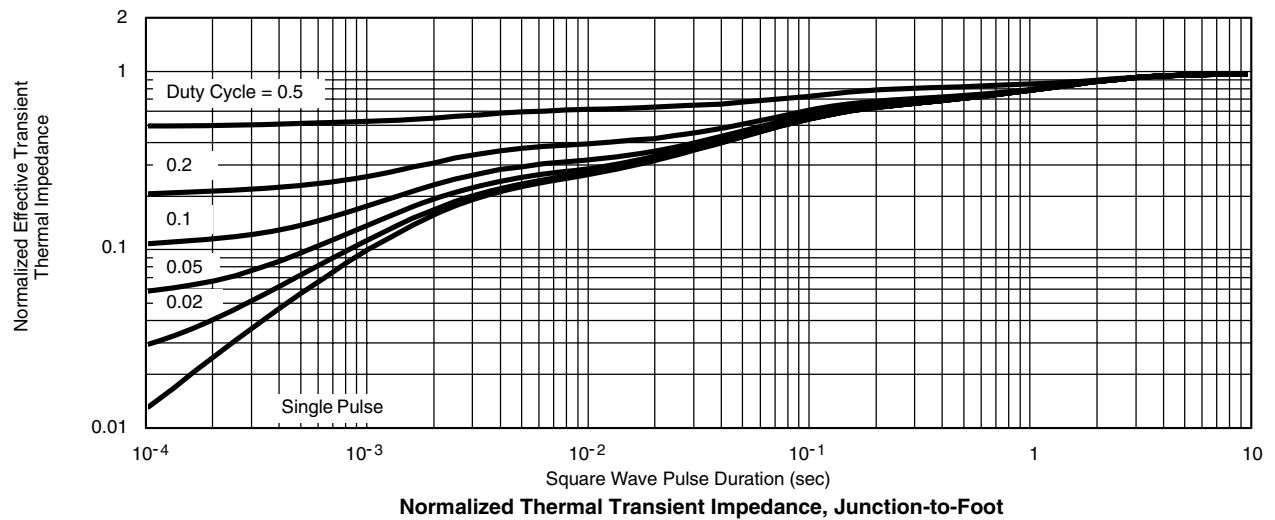
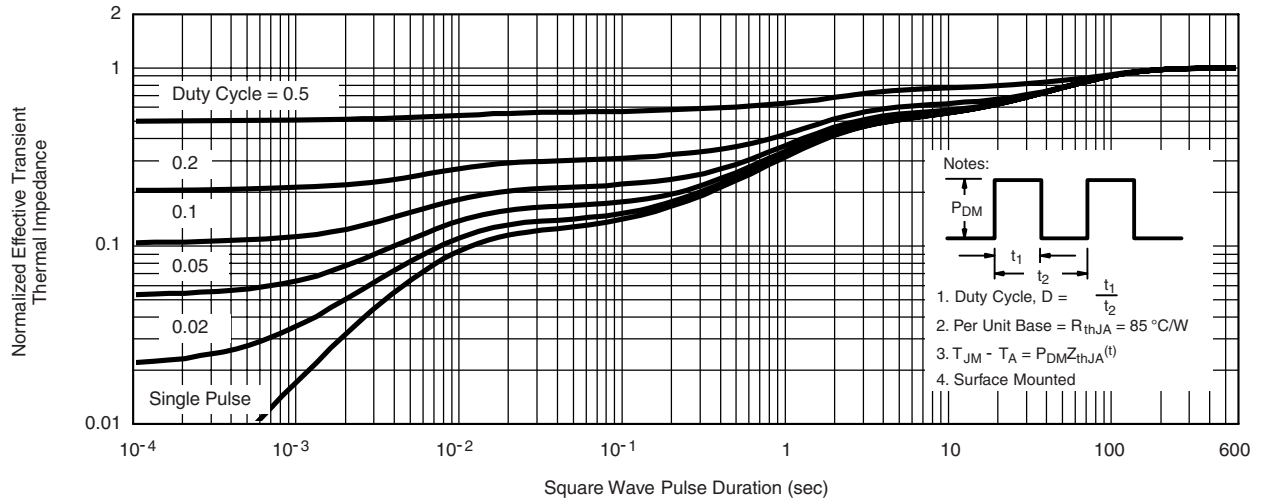


## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





**CHANNEL-2 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?74331>.



## Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.